



1765 #8/B
8/27/02

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Kichiya TANINO et al

Appln. No.: 09/771,556

Filed: January 30, 2001

For: SINGLE CRYSTAL SiC AND A
METHOD OF GROWING THE SAME

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) Art Unit: 1765
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) Ex: R.M. Kunemund
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RESPONSE TO NOTICE OF NON-COMPLIANT AMENDMENT (37 CFR 1.121)

Honorable Commissioner of Patents and Trademarks
Washington, D.C. 20231

Sir:

The following amendments to the specification are being submitted in response to
the Notice of Non-Compliant Amendment (37 CFR 1.121) dated July 17, 2002.

AMENDMENT

IN THE SPECIFICATION:

Please replace pages 4-7 (first four lines only of page 7) with the following:

--used, although such single crystal SiC has many features more excellent than existing
semiconductor materials such as Si and GaAs as described above.

Summary of the Invention

The invention has been conducted in view of the above-mentioned circumstances. It is an
object of the invention to provide single crystal SiC of high quality to which influence of

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